

RF LDMOS Wideband 2-Stage Power Amplifiers

Designed for broadband commercial and industrial applications with frequencies from 132 MHz to 960 MHz. The high gain and broadband performance of this device make it ideal for large-signal, common-source amplifier applications in 28 volt base station equipment. The device has a 2-stage design with off-chip matching for the input, interstage and output networks to cover the desired frequency band.

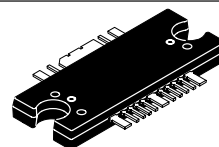
- Typical Performance: 800 MHz, 28 Volts, $I_{DQ1} = 80 \text{ mA}$,
 $I_{DQ2} = 650 \text{ mA}$, $P_{out} = 70 \text{ Watts PEP}$
Power Gain — 30 dB
Drain Efficiency — 48%
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 850 MHz, 70 Watts CW Output Power

Features

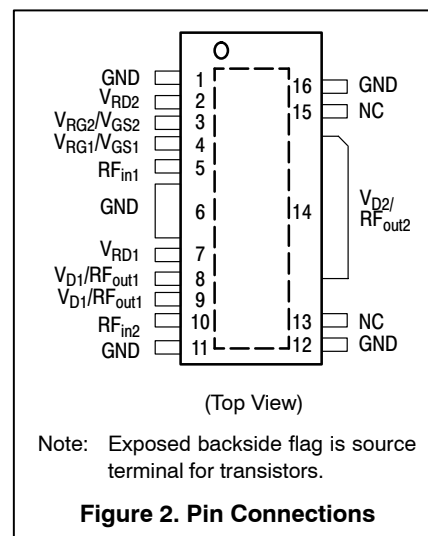
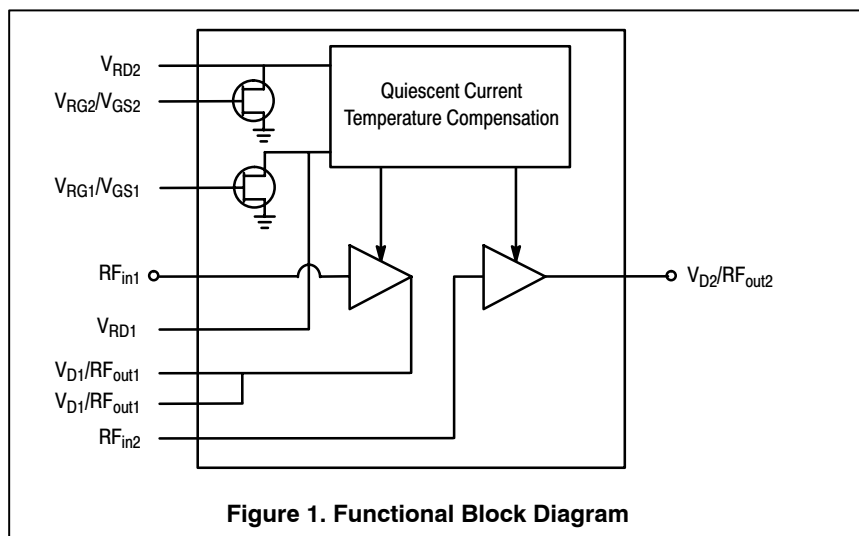
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Integrated Quiescent Current Temperature Compensation with Enable/Disable Function
- On-Chip Current Mirror g_m Reference FET for Self Biasing Application (1)
- Integrated ESD Protection
- 200°C Capable Plastic Package
- RoHS Compliant
- In Tape and Reel. R1 Suffix = 500 Units per 44 mm, 13 inch Reel.

MW5IC970NBR1

**800-900 MHz, 70 W, 28 V
RF LDMOS WIDEBAND
2-STAGE POWER AMPLIFIERS**



**CASE 1329-09
TO-272 WB-16
PLASTIC**



1. Refer to AN1987, *Quiescent Current Control for the RF Integrated Circuit Device Family*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1987.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	- 0.5, + 65	Vdc
Gate-Source Voltage	V_{GS}	- 0.5, + 15	Vdc
Storage Temperature Range	T_{stg}	- 65 to +200	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value ⁽¹⁾	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
Final Application ($P_{out} = 70$ W CW)	Stage 1, 28 Vdc, $I_{DQ} = 80$ mA Stage 2, 28 Vdc, $I_{DQ} = 650$ mA	5.2 0.8	
EDGE Application ($P_{out} = 35$ W CW)	Stage 1, 28 Vdc, $I_{DQ} = 80$ mA Stage 2, 28 Vdc, $I_{DQ} = 650$ mA	5.3 0.8	

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1A (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Moisture Sensitivity Level

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	3	260	°C

Table 5. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28.5$ Vdc, $I_{DQ1} = 80$ mA, $I_{DQ2} = 650$ mA, $P_{out} = 70$ W PEP, $f_1 = 870.0$ MHz, $f_2 = 870.1$ MHz

Power Gain	G_{ps}	26.5	30	34.5	dB
Drain Efficiency	η_D	40	48	—	%
Input Return Loss	IRL	—	-12	-10	dB
Intermodulation Distortion	IMD	—	-33	-28	dBc

Typical 800/900 MHz Performances (In Freescale 800/900 MHz Reference Fixture, 50 ohm system) $V_{DD} = 28$ Vdc, $I_{DQ1} = 80$ mA, $I_{DQ2} = 650$ mA, 740-870 MHz, 870-960 MHz

Gain Flatness in 30 MHz Bandwidth @ $P_{out} = 70$ W CW	G_F	—	2	—	dB
Gain Flatness in 30 MHz Instantaneous Bandwidth @ $P_{out} = 70$ W CW	G_F	—	0.2	—	dB
Delay @ $P_{out} = 70$ W CW Including Output Matching	Delay	—	4.5	—	ns
Part-to-Part Phase Variation @ $P_{out} = 70$ W CW	$\Delta\Phi$	—	± 15	—	°

1. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

(continued)



Table 6. MW5IC970NBR1 Test Circuit Component Designations and Values

MW5IC970NBR1

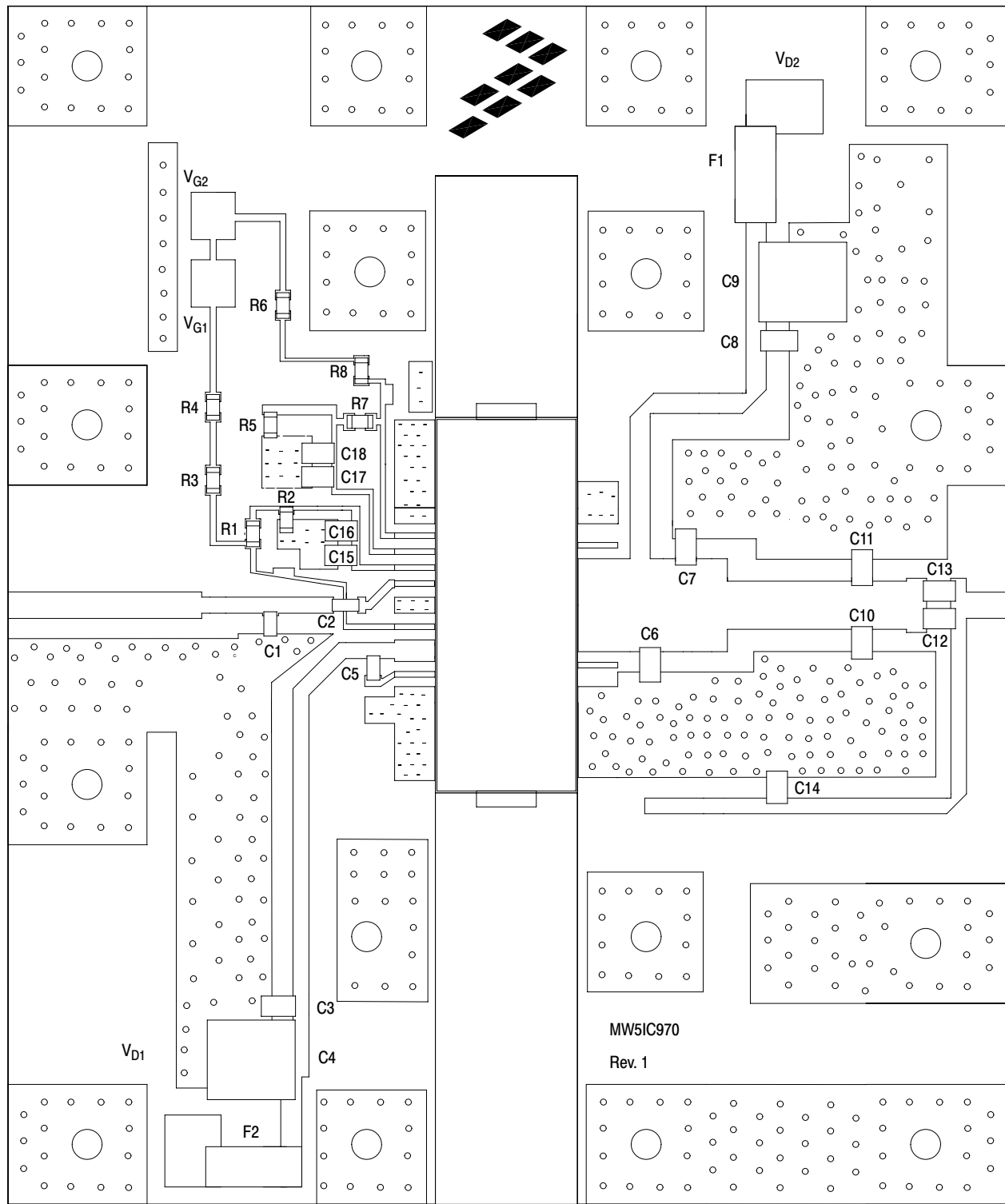


Figure 4. MW5IC970NBR1 Test Circuit Component Layout

TYPICAL CHARACTERISTICS

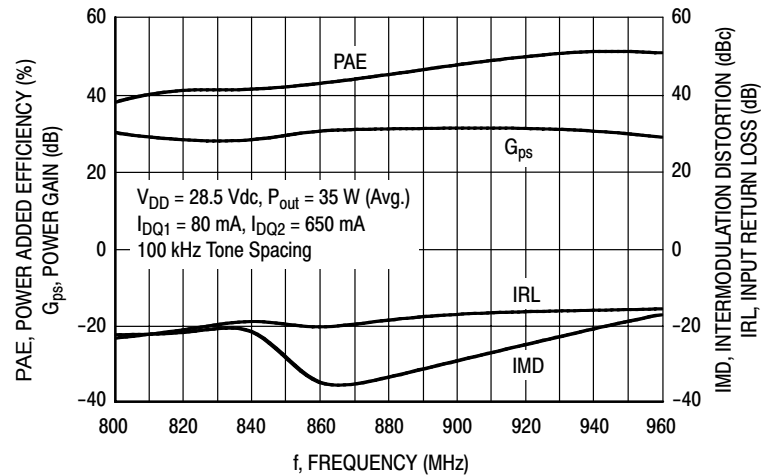


Figure 5. Two-Tone Wideband Performance
@ $P_{out} = 35$ Watts (Avg.)

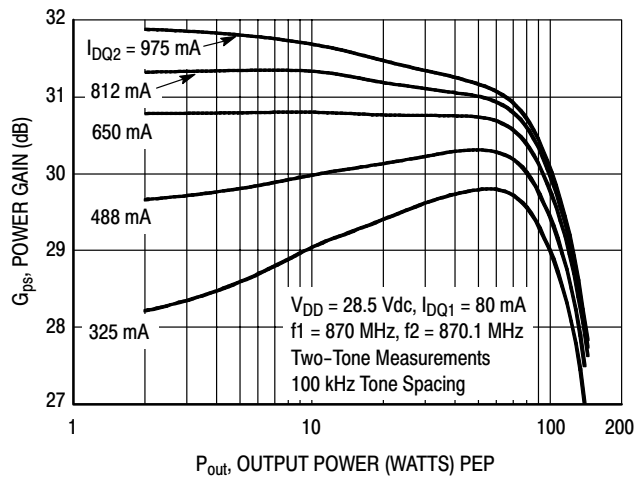


Figure 6. Two-Tone Power Gain versus Output Power

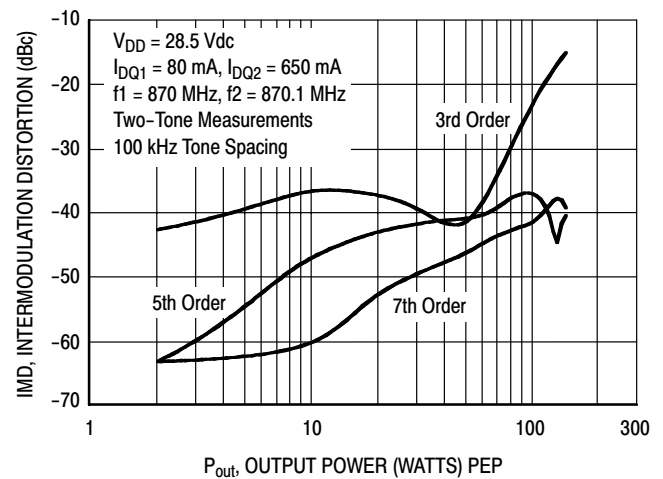


Figure 7. Intermodulation Distortion Products versus Output Power

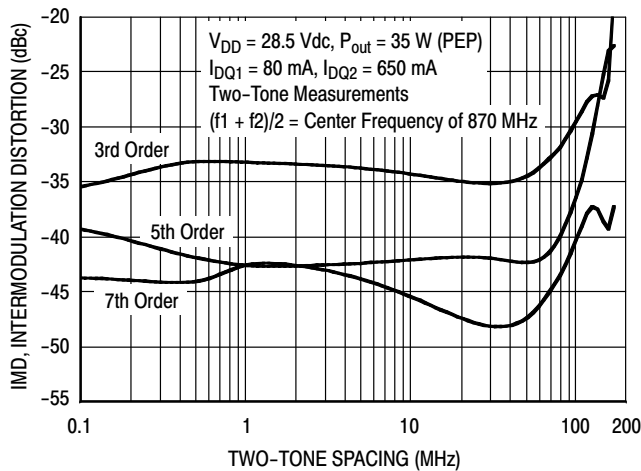


Figure 8. Intermodulation Distortion Products versus Tone Spacing

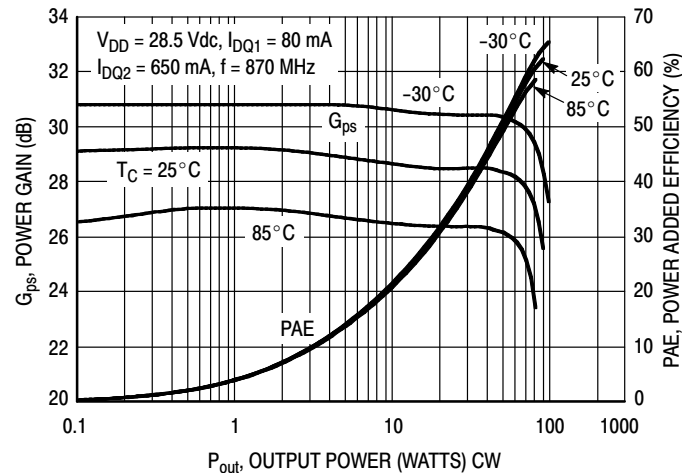


Figure 9. Power Gain and Power Added Efficiency versus CW Output Power

TYPICAL CHARACTERISTICS

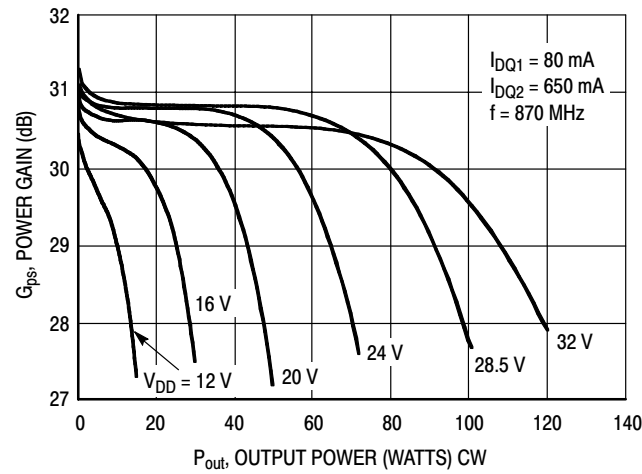


Figure 10. Power Gain versus Output Power

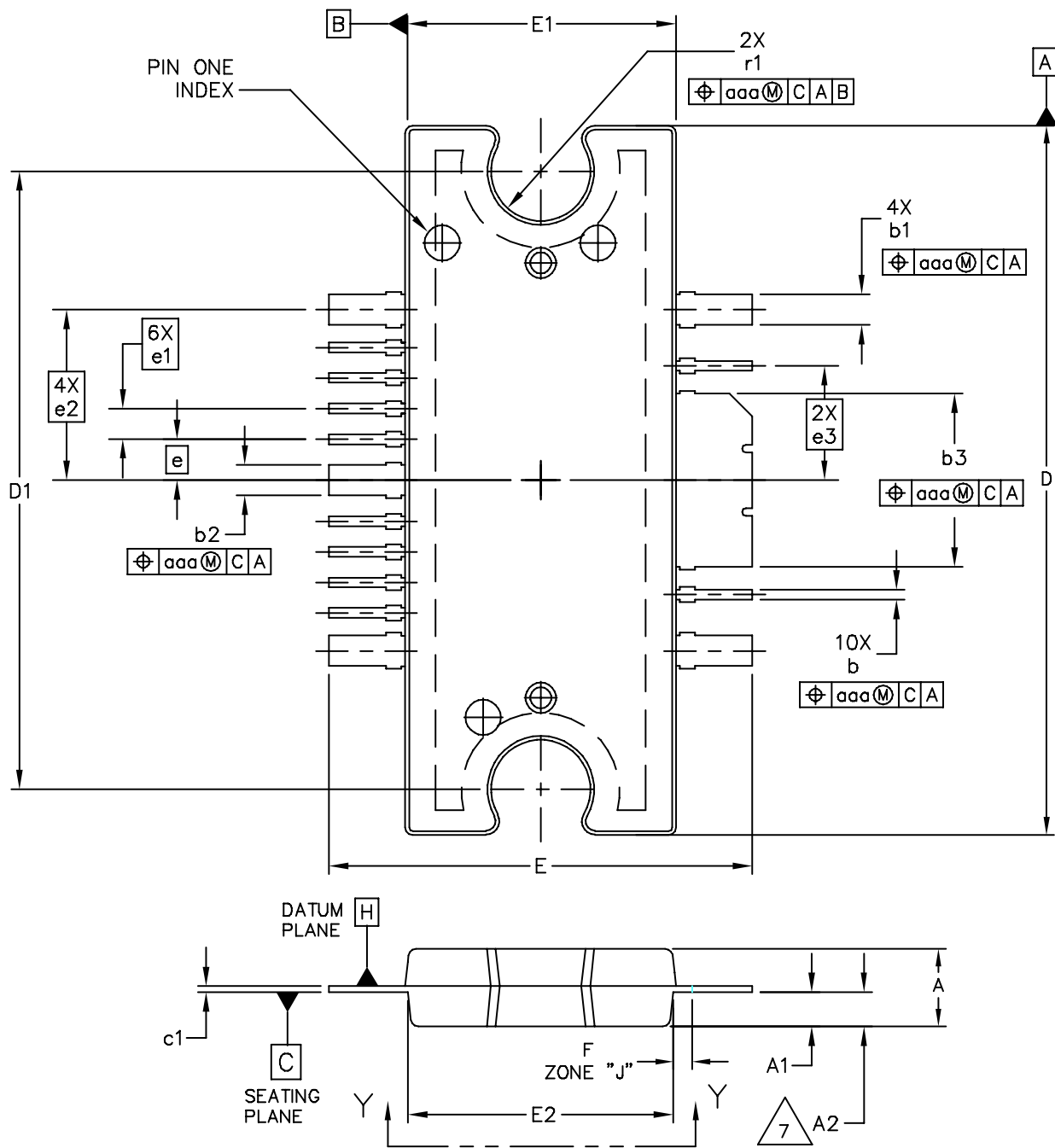


NOTES

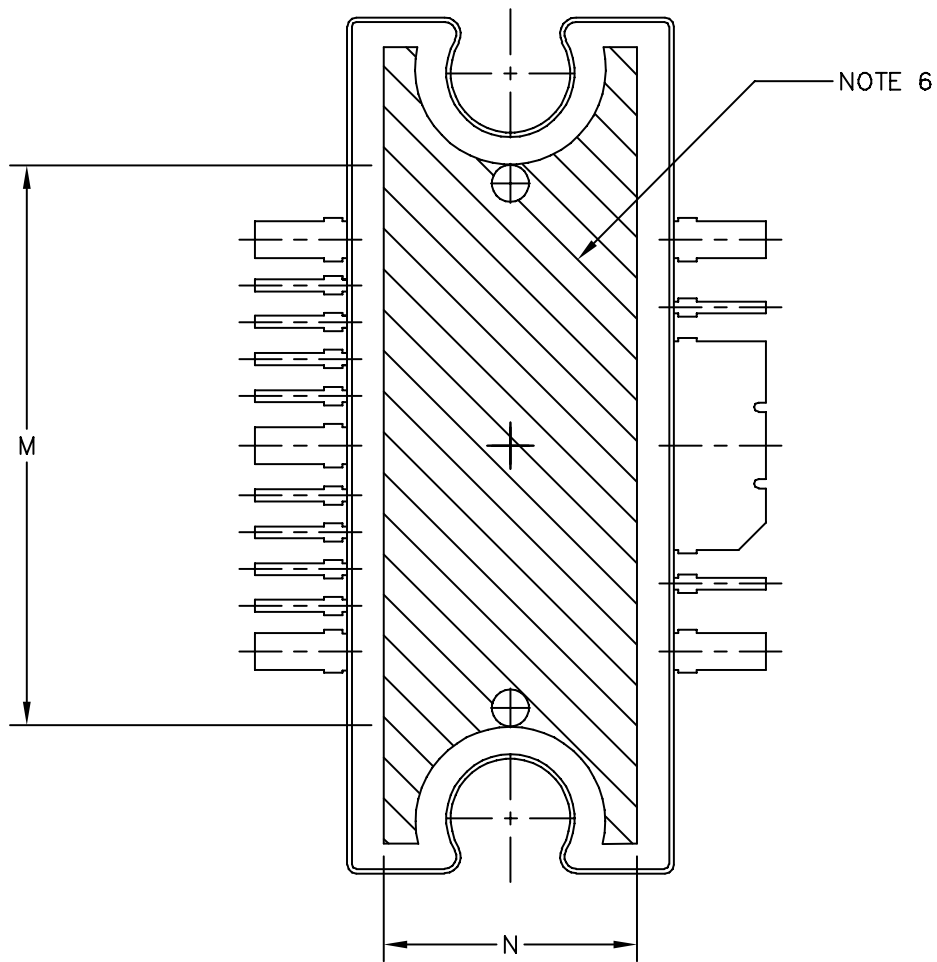


NOTES

PACKAGE DIMENSIONS



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			CASE NUMBER: 1329-09		13 MAR 2006
			STANDARD: NON-JEDEC		



VIEW Y-Y

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			CASE NUMBER: 1329-09		13 MAR 2006
			STANDARD: NON-JEDEC		

NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 (0.15) PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSIONS "b", "b1", "b2" AND "b3" DO NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 (0.13) TOTAL IN EXCESS OF THE "b", "b1", "b2" AND "b3" DIMENSIONS AT MAXIMUM MATERIAL CONDITION.
6. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG. HATCHED AREA SHOWN IS ON THE SAME PLANE.
7. DIM A2 APPLIES WITHIN ZONE "J" ONLY.

INCH			MILLIMETER		INCH			MILLIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64	b	.011	.017	0.28	0.43
A1	.038	.044	0.96	1.12	b1	.037	.043	0.94	1.09
A2	.040	.042	1.02	1.07	b2	.037	.043	0.94	1.09
D	.928	.932	23.57	23.67	b3	.225	.231	5.72	5.87
D1	.810 BSC		20.57 BSC		c1	.007	.011	.18	.28
E	.551	.559	14.00	14.20	e	.054 BSC		1.37 BSC	
E1	.353	.357	8.97	9.07	e1	.040 BSC		1.02 BSC	
E2	.346	.350	8.79	8.89	e2	.224 BSC		5.69 BSC	
F	.025 BSC		0.64 BSC		e3	.150 BSC		3.81 BSC	
M	.600	----	15.24	----	r1	.063	.068	1.6	1.73
N	.270	----	6.86	----	aaa	.004		.10	
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